

HM6287 Series

Maintenance Only

65536-word x 1-bit High Speed CMOS Static RAM

Refer to HM6287H Series

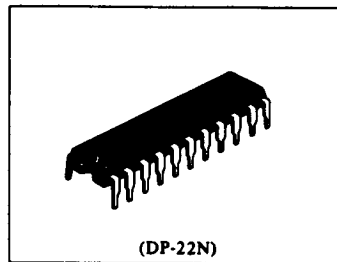
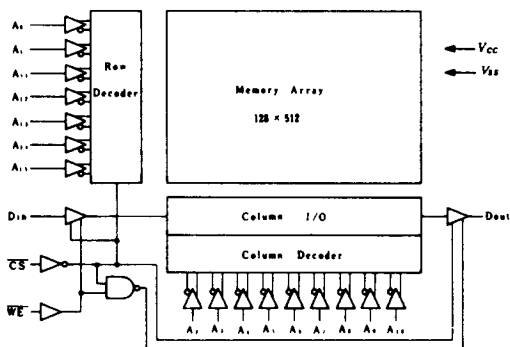
■ FEATURES

- High Speed: Fast Access Time 45/55/70ns (max.)
- Single 5V Supply and High Density 22 Pin Package
- Low Power Standby and Low Power Operation
Standby: 100 μ W (typ.)/10 μ W (typ.) (L-version)
Operation: 300mW (typ.)
- Completely Static Memory
No Clock or Timing Strobe Required
- Equal Access and Cycle Times
- Directly TTL Compatible: All Inputs and Output
- Capability of Battery Back Up Operation (L-version)

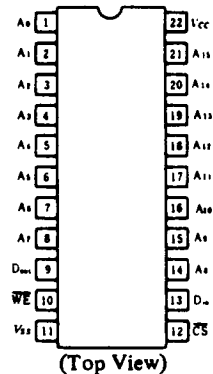
■ ORDERING INFORMATION

Type No.	Access Time	Package
HM6287P-45	45ns	300 mil 22 pin Plastic DIP
HM6287P-55	55ns	
HM6287P-70	70ns	
HM6287LP-45	45ns	
HM6287LP-55	55ns	
HM6287LP-70	70ns	

■ BLOCK DIAGRAM



■ PIN ARRANGEMENT



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■ TRUTH TABLE

CS	WE	Mode	V_{CC} Current	Dout Pin	Ref. Cycle
H	X	Not Selected	I_{SB}, I_{SB1}	High Z	—
L	H	Read	I_{CC}	Dout	Read Cycle
L	L	Write	I_{CC}	High Z	Write Cycle

■ ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Voltage on Any Pin Relative to V_{SS}	V_T	-0.5 ^{*1} to +7.0	V
Power Dissipation	P_T	1.0	W
Operating Temperature	T_{opr}	0 to +70	°C
Storage Temperature	T_{stg}	-55 to +125	°C
Temperature Under Bias	T_{bias}	-10 to +85	°C

Note) *1. -3.5V for pulse width ≤ 20 ns

■ RECOMMENDED DC OPERATING CONDITIONS ($T_a = 0$ to +70°C)

Item	Symbol	min	typ	max	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input Voltage	V_{IH}	2.2	—	6.0	V
	V_{IL}	-0.5 ^{*1}	—	0.8	V

Note) *1. -3.0V for pulse width ≤ 20 ns

■ DC AND OPERATING CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $V_{SS} = 0V$, $T_a = 0$ to +70°C)

Item	Symbol	Test Conditions	min	typ ^{*1}	max	Unit
Input Leakage Current	$ I_{LI} $	$V_{CC} = 5.5V$, $V_{in} = V_{SS}$ to V_{CC}	—	—	2.0	μA
Output Leakage Current	$ I_{LO} $	$\overline{CS} = V_{IH}$, $V_{out} = V_{SS}$ to V_{CC}	—	—	2.0	μA
Operating Power Supply Current	I_{CC}	$\overline{CS} = V_{IL}$, $I_{out} = 0mA$, min. cycle	—	60	100	mA
Standby Power Supply Current	I_{SB}	$\overline{CS} = V_{IH}$, min. cycle	—	10	30	mA
	I_{SB1}	$\overline{CS} \geq V_{CC} - 0.2V$, $0V \leq V_{in} \leq 0.2V$ or $V_{CC} - 0.2V \leq V_{in}$	—	0.02	2.0	mA
Output Voltage	V_{OL}	$I_{OL} = 8mA$	—	—	0.4	V
	V_{OH}	$I_{OH} = -4.0mA$	2.4	—	—	V

Notes) *1. Typical limits are at $V_{CC} = 5.0V$, $T_a = 25^\circ C$ and specified loading.

*2. This characteristics is guaranteed only for L-version.

■ CAPACITANCE ($f = 1MHz$, $T_a = 25^\circ C$)

Item	Symbol	Test Conditions	min	typ	max	Unit
Input Capacitance	C_{in}	$V_{in} = 0V$	—	—	5	pF
Output Capacitance	C_{out}	$V_{out} = 0V$	—	—	7.5	pF

Note) This parameter is sampled and not 100% tested.



■ AC CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $T_a = 0$ to $+70^\circ\text{C}$, unless otherwise noted)

● AC TEST CONDITIONS

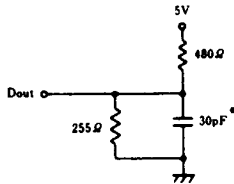
Input Pulse Levels: V_{SS} to 3.0V

Input Rise and Fall Times: 5ns

Input and Output Timing Reference Levels: 1.5V

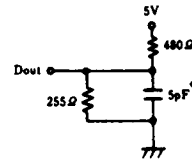
Output Load: See Figure

Output Load A



*Including scope & jig capacitance

Output Load B

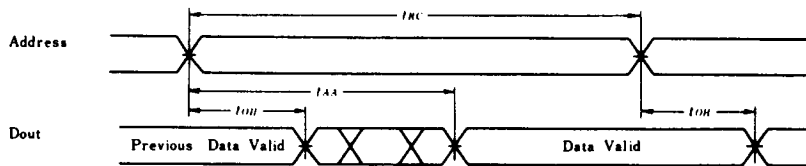


*Including scope & jig capacitance

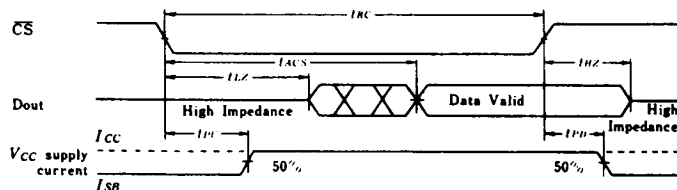
● READ CYCLE

Item	Symbol	HM6287-45		HM6287-55		HM6287-70		Unit	Notes
		min	max	min	max	min	max		
Read Cycle Time	t_{RC}	45	—	55	—	70	—	ns	1
Address Access Time	t_{AA}	—	45	—	55	—	70	ns	
Chip Select Access Time	t_{ACS}	—	45	—	55	—	70	ns	
Output Hold from Address Change	t_{OH}	5	—	5	—	5	—	ns	
Chip Selection to Output in Low Z	t_{LZ}	5	—	5	—	5	—	ns	2, 3, 7
Chip Deselection to Output in High Z	t_{HZ}	0	30	0	30	0	30	ns	2, 3, 7
Chip Selection to Power Up Time	t_{PU}	0	—	0	—	0	—	ns	7
Chip Deselection to Power Down Time	t_{PD}	—	40	—	40	—	40	ns	7

● Timing Waveform of Read Cycle No. 1⁽⁴⁾⁽⁵⁾



● Timing Waveform of Read Cycle No. 2⁽⁴⁾⁽⁶⁾



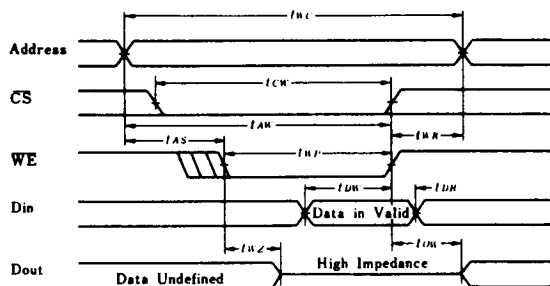
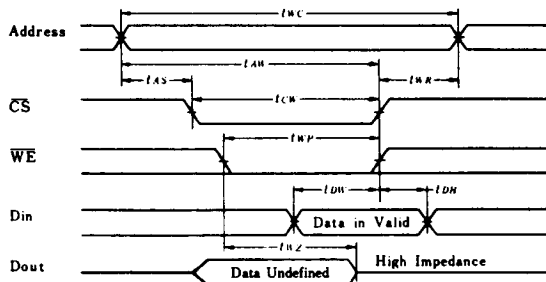
- Notes:
1. All Read Cycle timings are referenced from last valid address to the first transitioning address.
 2. At any given temperature and voltage condition, t_{HZ} max. is less than t_{LZ} min. both for a given device and from device to device.
 3. Transition is measured ± 500 mV from steady state voltage with specified loading in Load B.
 4. $\overline{WE}$ is high for READ Cycle.
 5. Device is continuously selected, while $\overline{CS} = V_{IL}$.
 6. Address valid prior to or coincident with $\overline{CS}$ transition low.
 7. This parameter is sampled and not 100% tested.



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● WRITE CYCLE

Item	Symbol	HM6287-45		HM6287-55		HM6287-70		Unit	Notes
		min	max	min	max	min	max		
Write Cycle Time	t_{WC}	45	—	55	—	70	—	ns	2
Chip Selection to End of Write	t_{CW}	40	—	50	—	55	—	ns	
Address Valid to End of Write	t_{AW}	40	—	50	—	55	—	ns	
Address Setup Time	t_{AS}	0	—	0	—	0	—	ns	
Write Pulse Width	t_{WP}	25	—	35	—	40	—	ns	
Write Recovery Time	t_{WR}	0	—	0	—	0	—	ns	
Data Valid to End of Write	t_{DW}	25	—	25	—	30	—	ns	
Data Hold Time	t_{DH}	0	—	0	—	0	—	ns	
Write Enabled to Output in High Z	t_{WZ}	0	25	0	25	0	30	ns	3, 4
Output Active from End of Write	t_{OW}	0	—	0	—	0	—	ns	3, 4

● Timing Waveform of Write Cycle No. 1 ($\overline{WE}$ Controlled)● Timing Waveform of Write Cycle No. 1 ($\overline{CS}$ Controlled)

- Notes)
1. If $\overline{CS}$ goes high Simultaneously with $\overline{WE}$ high, the output remains in a high impedance state.
 2. All Write Cycle timings are referenced from the last valid address to the first transitioning address.
 3. Transition is measured $\pm 500\text{mV}$ from steady state voltage with specified loading in Load B.
 4. This parameter is sampled and not 100% tested.



■ **LOW V_{CC} DATA RETENTION CHARACTERISTICS** ($T_a = 0$ to $+70^\circ\text{C}$)

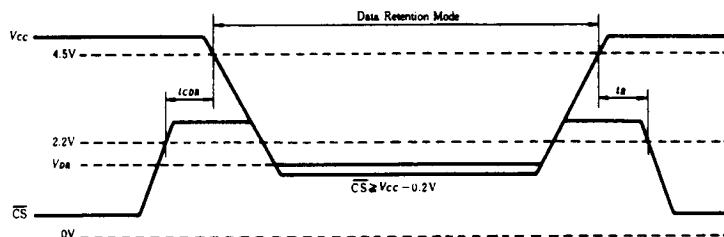
This characteristics is guaranteed only for L-version.

Parameter	Symbol	Test Condition	min.	typ.	max.	Unit
V_{CC} for Data Retention	V_{DR}	$CS \geq V_{CC} - 0.2\text{V}$ $V_{in} \leq V_{CC} - 0.2\text{V}$ or $0\text{V} \leq V_{in} \leq 0.2\text{V}$	2.0	—	—	V
Data Retention Current	I_{CCDR}		—	1	50^{*2}	μA
Chip Deselect to Data Retention Time	t_{CDR}	See retention waveform	0	—	—	ns
Operation Recovery Time	t_R		t_{RC}^{*1}	—	—	ns

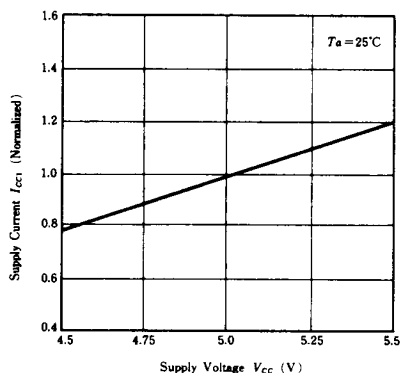
Note) *1. t_{RC} = Read Cycle Time

*2. $V_{CC} = 3.0\text{V}$

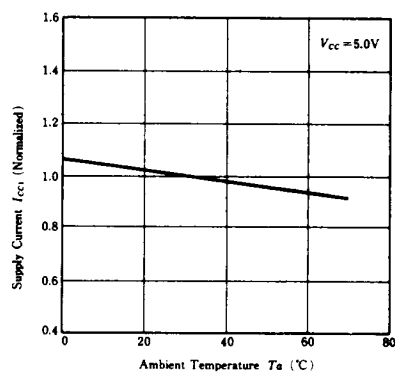
● **LOW V_{CC} DATA RETENTION WAVEFORM**



SUPPLY CURRENT vs. SUPPLY VOLTAGE

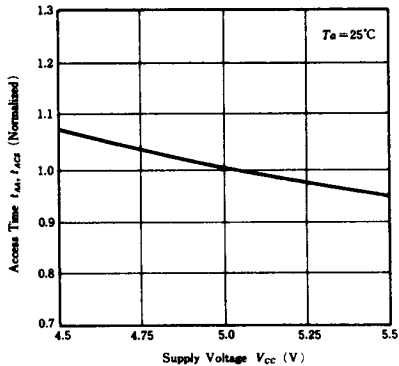


SUPPLY CURRENT vs. AMBIENT TEMPERATURE

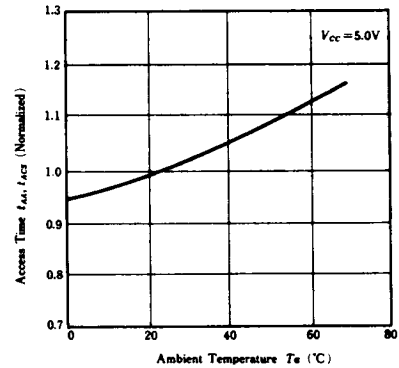


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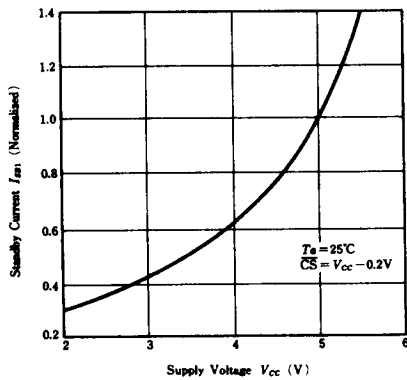
ACCESS TIME vs. SUPPLY VOLTAGE



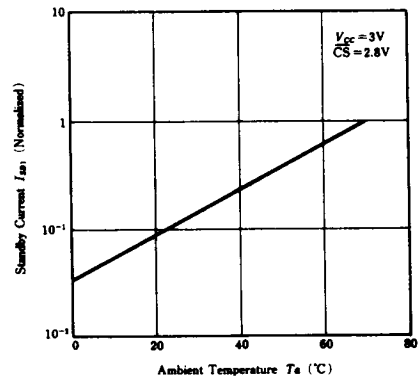
ACCESS TIME vs. AMBIENT TEMPERATURE



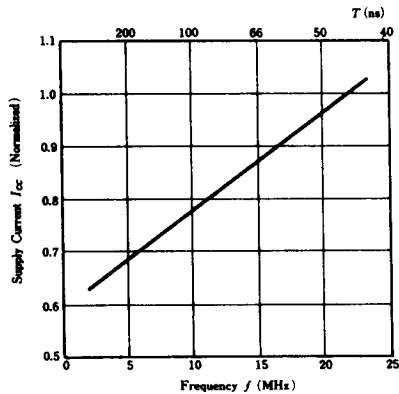
STANDBY CURRENT vs. SUPPLY VOLTAGE



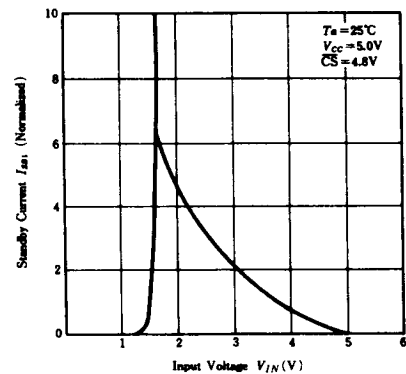
STANDBY CURRENT vs. AMBIENT TEMPERATURE

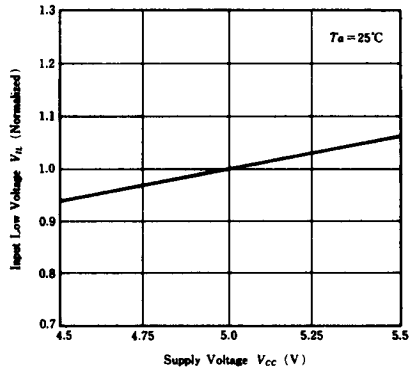
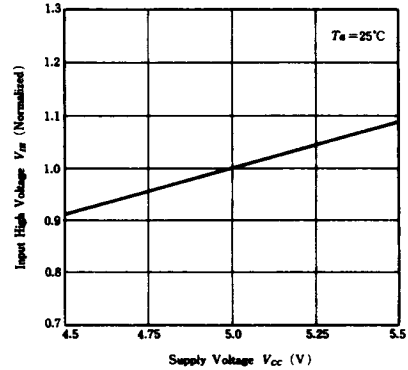
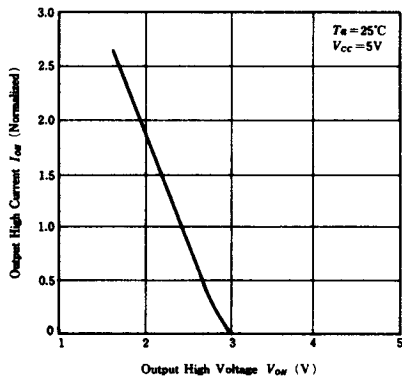


SUPPLY CURRENT vs. FREQUENCY



STANDBY CURRENT vs. INPUT VOLTAGE



**INPUT LOW VOLTAGE vs.
SUPPLY VOLTAGE****INPUT HIGH VOLTAGE vs.
SUPPLY VOLTAGE****OUTPUT HIGH CURRENT vs.
OUTPUT HIGH VOLTAGE****OUTPUT LOW CURRENT vs.
OUTPUT LOW VOLTAGE**